High-Current Complementary Silicon Power Transistors

These packages are designed for use in high-power amplifier and switching circuit applications.

Features

- High Current Capability I_C Continuous = 50 Amperes
- DC Current Gain h_{FE} = 15 60 @ I_C = 25 Adc
- Low Collector-Emitter Saturation Voltage –
 V_{CE(sat)} = 1.0 Vdc (Max) @ I_C = 25 Adc
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Note 1)

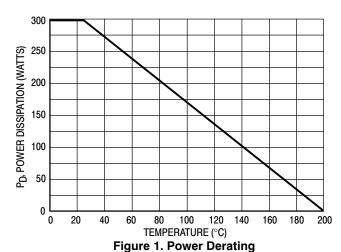
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CB}	80	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous	I _C	50	Adc
Base Current	I _B	15	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	300 1.715	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θЈС	0.584	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data.





ON Semiconductor®

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50 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60-80 VOLTS, 300 WATTS

MARKING DIAGRAM





TO-204 (TO-3) CASE 197A STYLE 1

2N568x = Device Code

x = 4 or 6

G = Pb-Free Package A = Location Code

YY = Year WW = Work Week MEX = Country of Orgin

ORDERING INFORMATION

Device	Package	Shipping
2N5684G	TO-3 (Pb-Free)	100 Units/Tray
2N5686	TO-3	100 Units/Tray
2N5686G	TO-3 (Pb-Free)	100 Units/Tray

Safe Area Curves are indicated by Figure 5. All limits are applicable and must be observed.

October, 2007 - Rev. 12

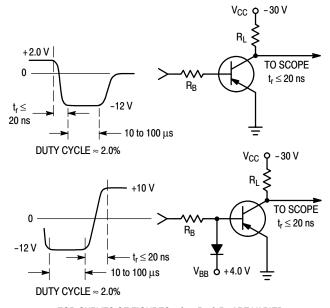
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (Note 2)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS		1	•	•	
Collector-Emitter Sustaining Voltage (Note	3) $(I_C = 0.2 \text{ Adc}, I_B = 0)$	V _{CEO(sus)}	80	-	Vdc
Collector Cutoff Current	(V _{CE} = 40 Vdc, I _B = 0)	I _{CEO}	-	1.0	mAdc
Collector Cutoff Current (V _{CE} =	(V _{CE} = 80 Vdc, V _{EB(off)} = 1.5 Vdc) = 80 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C)	I _{CEX}	- -	2.0 10	mAdc
Collector Cutoff Current	(V _{CB} = 80 Vdc, I _E = 0)	I _{CBO}	-	2.0	mAdc
Emitter Cutoff Current	$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	-	5.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3)	$(I_C = 25 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc})$ $(I_C = 50 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$	h _{FE}	15 5.0	60 -	-
Collector-Emitter Saturation Voltage (Note:	3) $ (I_{C} = 25 \text{ Adc}, I_{B} = 2.5 \text{ Adc}) $ $ (I_{C} = 50 \text{ Adc}, I_{B} = 10 \text{ Adc}) $	V _{CE(sat)}	- -	1.0 5.0	Vdc
Base-Emitter Saturation Voltage (Note 2)	(I _C = 25 Adc, I _B = 2.5 Adc)	V _{BE(sat)}	-	2.0	Vdc
Base-Emitter On Voltage (Note 2)	(I _C = 25 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	2.0	Vdc
DYNAMIC CHARACTERISTICS					•
Current-Gain - Bandwidth Product (I _C = 5.0 Adc, V _{CE} = 10 Vdc, f = 1.0 MHz)	f _T	2.0	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	2N5684 2N5686	C _{ob}	- -	2000 1200	pF
Small-Signal Current Gain	(I _C = 10 Adc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	h _{fe}	15	-	

^{2.} Indicates JEDEC Registered Data.

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



FOR CURVES OF FIGURES 3 & 6, $\rm R_B$ & $\rm R_L$ ARE VARIED. INPUT LEVELS ARE APPROXIMATELY AS SHOWN. FOR NPN CIRCUITS, REVERSE ALL POLARITIES.

Figure 2. Switching Time Test Circuit

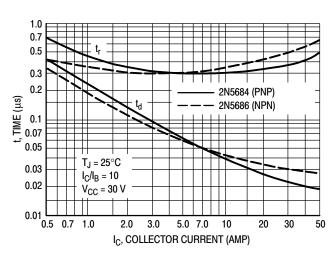


Figure 3. Turn-On Time

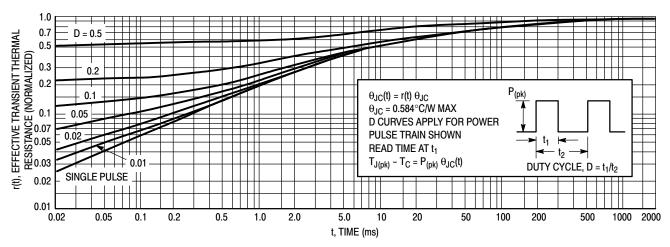


Figure 4. Thermal Response

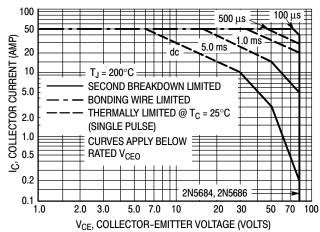


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 200^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

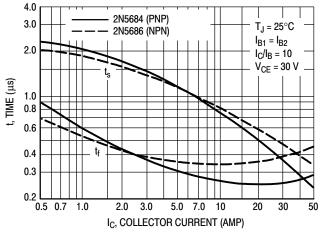


Figure 6. Turn-Off Time

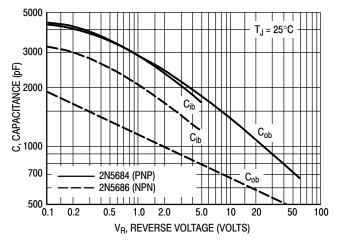


Figure 7. Capacitance

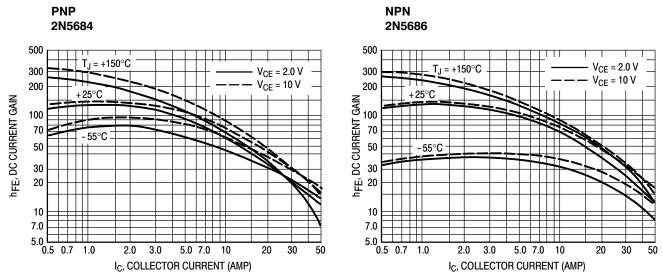


Figure 8. DC Current Gain

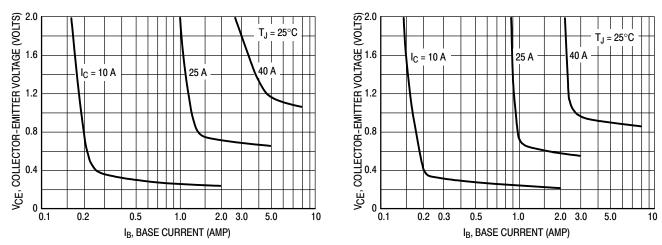


Figure 9. Collector Saturation Region

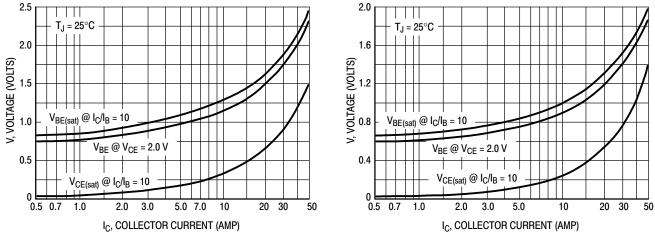
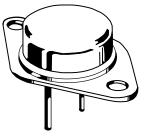


Figure 10. "On" Voltages

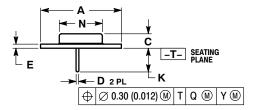


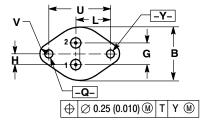


TO-204 (TO-3) **CASE 197A-05 ISSUE K**

DATE 21 FEB 2000

SCALE 1:1





STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

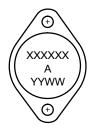
STYLE 2: PIN 1. EMITTER 2. BASE CASE: COLLECTOR STYLE 3: PIN 1. GATE 2. SOURCE CASE: DRAIN

STYLE 4: PIN 1. ANODE = 1 2. ANODE = 2 CASE: CATHODES

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	1.530	REF	38.86 REF	
В	0.990	1.050	25.15	26.67
С	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
Е	0.060	0.070	1.53	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215 BSC		5.46	BSC
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89	BSC
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
٧	0.131	0.188	3.33	4.77

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Locationa Α

YY = Year WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking.

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PAGE 2 OF 2

ISSUE	REVISION	DATE
K	LEGALLY CHANGED TO ON	21 FEB 2000

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